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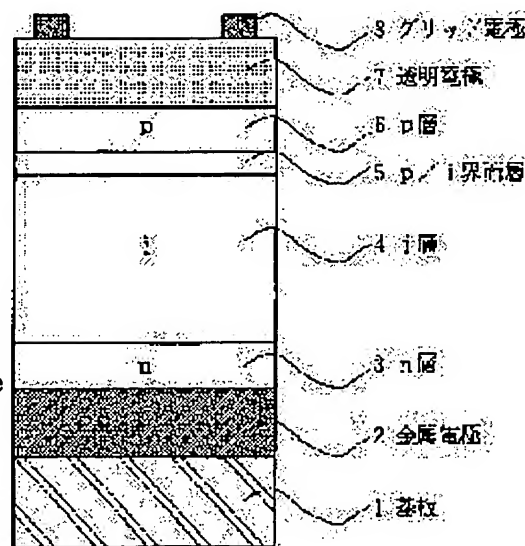
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(54) AMORPHOUS THIN FILM SOLAR CELL AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To enhance the efficiency of an amorphous thin film solar cell having at least one pin junction formed of a p-type semiconductor layer or an n-type semiconductor layer comprising an amorphous thin film including a microcrystalline phase, a substantially intrinsic i-type semiconductor layer comprising an amorphous thin film, or an n-type semiconductor layer or a p-type semiconductor layer comprising an amorphous thin film.
SOLUTION: A p/i interface layer 5 of amorphous silicon oxide having thickness of 1 to 8 nm is provided between a p-type semiconductor layer 6 comprising an amorphous thin film including a microcrystalline phase and an intrinsic i-type semiconductor layer 4.



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